



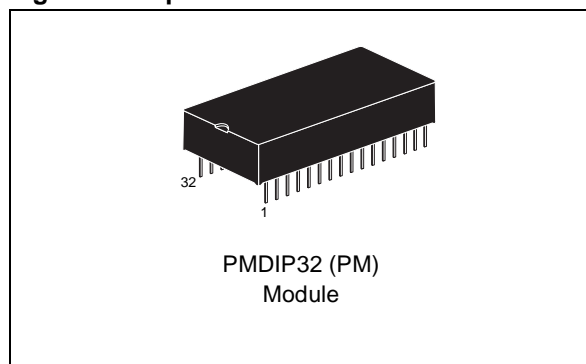
# M48Z512A M48Z512AY, M48Z512AV\*

4 Mbit (512 Kbit x 8) ZEROPOWER<sup>®</sup> SRAM

## FEATURES SUMMARY

- INTEGRATED, ULTRA LOW POWER SRAM, POWER-FAIL CONTROL CIRCUIT, and BATTERY
- CONVENTIONAL SRAM OPERATION; UNLIMITED WRITE CYCLES
- 10 YEARS OF DATA RETENTION IN THE ABSENCE OF POWER
- AUTOMATIC POWER-FAIL CHIP DESELECT and WRITE PROTECTION
- TWO WRITE PROTECT VOLTAGES: ( $V_{PFD}$  = Power-fail Deselect Voltage)
  - M48Z512A:  $V_{CC} = 4.75$  to  $5.5V$   
 $4.5V \leq V_{PFD} \leq 4.75V$
  - M48Z512AY:  $V_{CC} = 4.5$  to  $5.5V$   
 $4.2V \leq V_{PFD} \leq 4.5V$
  - M48Z512AV:  $V_{CC} = 3.0$  to  $3.6V$   
 $2.8V \leq V_{PFD} \leq 3.0V$
- BATTERY INTERNALLY ISOLATED UNTIL POWER IS APPLIED
- PIN and FUNCTION COMPATIBLE WITH JEDEC STANDARD 512K x 8 SRAMs
- SOIC PACKAGE PROVIDES DIRECT CONNECTION FOR A SNAPHAT TOP WHICH CONTAINS THE BATTERY
- SNAPHAT HOUSING (BATTERY) IS REPLACEABLE
- EQUIVALENT SURFACE-MOUNT (SMT) SOLUTION REQUIRES A 28-PIN M40Z300/W and A STAND-ALONE 128K x8 LPSRAM (SNAPHAT<sup>®</sup> Top to be ordered separately)

Figure 1. 32-pin PMDIP Module



\* Contact Local Sales Office

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**DESCRIPTION**

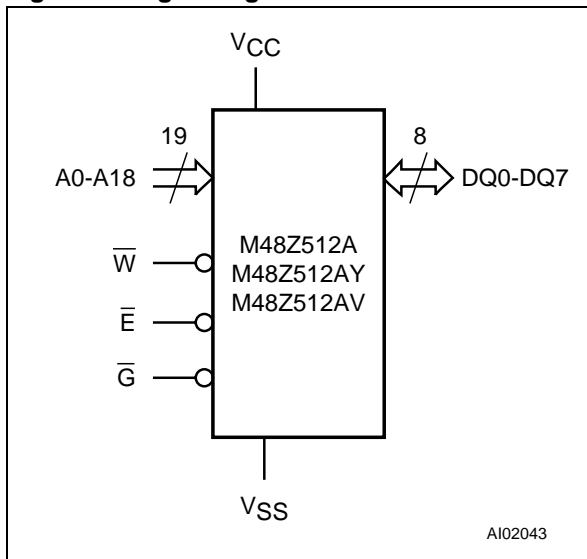
The M48Z512A/Y/V ZEROPOWER® RAM is a non-volatile, 4,194,304-bit Static RAM organized as 524,288 words by 8 bits. The device combines an internal lithium battery, a CMOS SRAM and a control circuit in a plastic, 32-pin DIP Module.

For surface-mount environments ST provides an equivalent SMT solution consisting of a 28-pin, 330mil SOIC NVRAM SUPERVISOR (M40Z300/W) and a 32-pin, (Type II TSOP, 10 x 20mm) 4Mb LPSRAM. Both 5V and 3V versions are available (see Table 2, page 5).

The unique design allows the SNAPHAT® battery package to be mounted on top of the SOIC package after the completion of the surface-mount process. Insertion of the SNAPHAT housing after reflow prevents potential battery damage due to the high temperatures required for device surface-mounting. The SNAPHAT housing is keyed to prevent reverse insertion.

The SNAPHAT battery package is shipped separately in plastic anti-static tubes or in Tape & Reel form. The part number is "M4Z32-BR00SH1."

**Figure 2. Logic Diagram**



**Table 1. Signal Names**

A0-A18	Address Inputs
DQ0-DQ7	Data Inputs / Outputs
$\bar{E}$	Chip Enable Input
$\bar{G}$	Output Enable Input
$\bar{W}$	WRITE Enable Input
VCC	Supply Voltage
VSS	Ground

Figure 3. DIP Connections

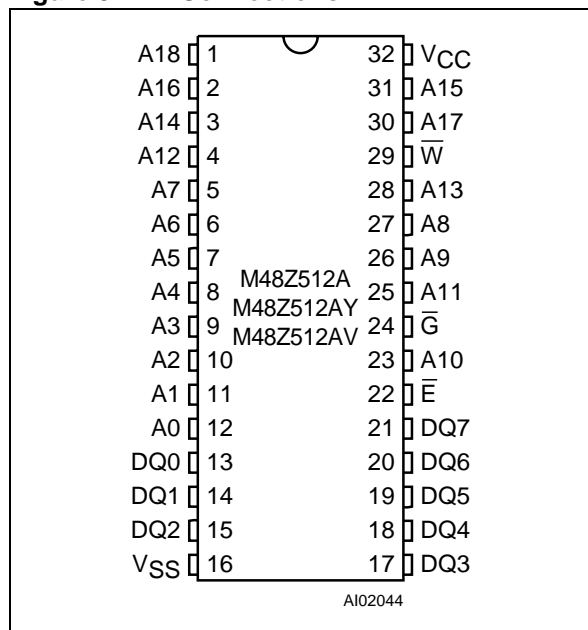


Figure 4. Block Diagram

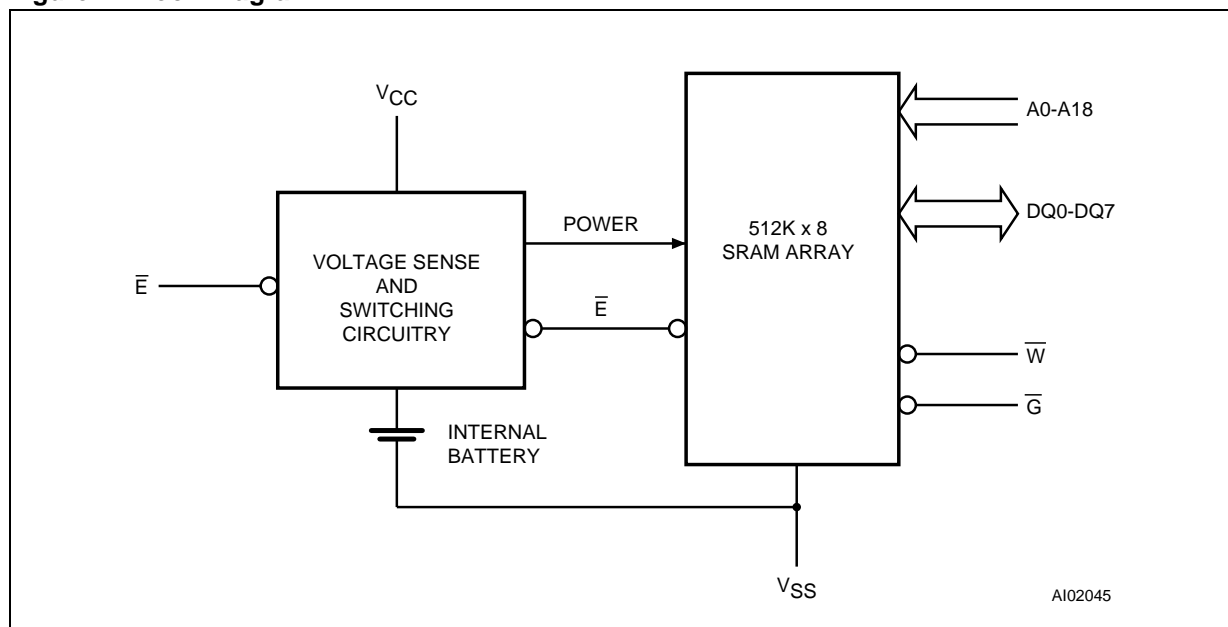
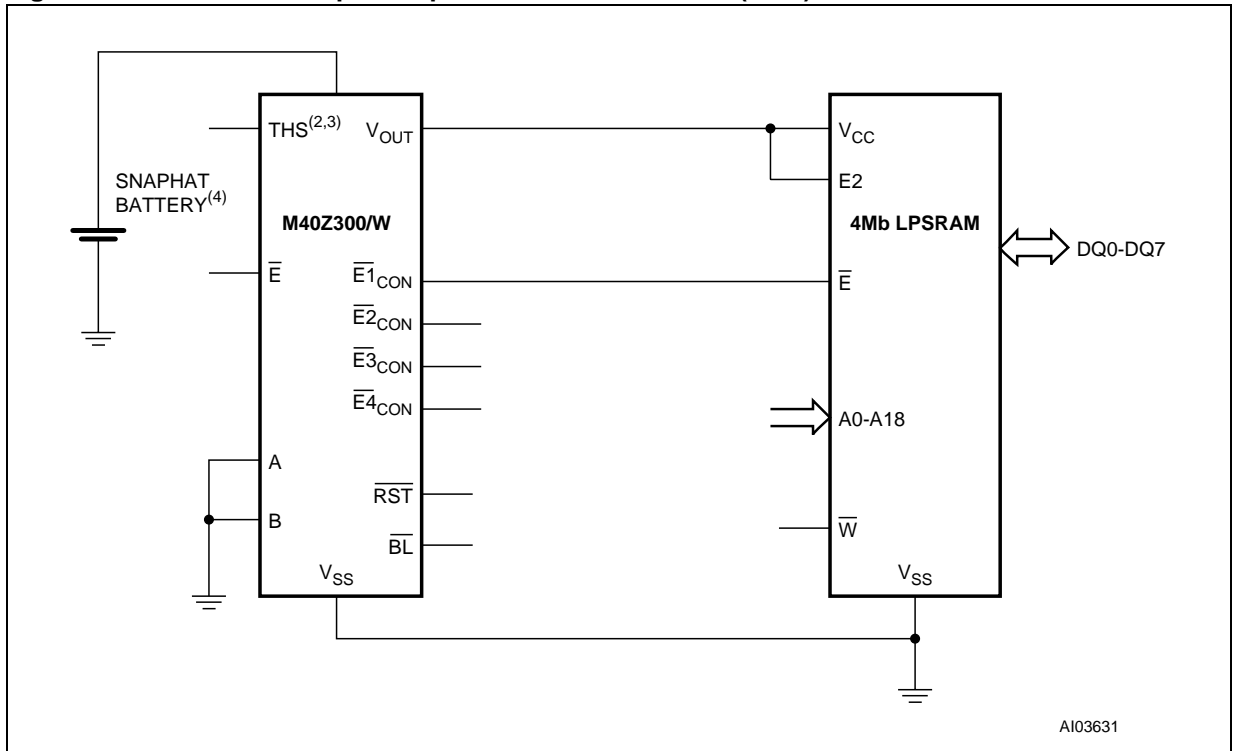


Figure 5. Hardware Hookup for Equivalent Surface-Mount (SMT) Solution



Note: For pin connections, see individual datasheet for M48Z300/300W at [www.st.com](http://www.st.com).

1. Connect THS pin to V<sub>OUT</sub> if  $4.2V \leq V_{PFD} \leq 4.5V$  (M48Z512AY) or connect THS pin to V<sub>SS</sub> if  $4.5V \leq V_{PFD} \leq 4.75V$  (M48Z512A).
2. Connect THS pin to V<sub>SS</sub> if  $2.8V \leq V_{PFD} \leq 3.0V$  (M48Z512AV).
3. SNAPHAT® Top ordered separately.

Table 2. Equivalent Surface-Mount (SMT) Solution

NVRAM	LPSRAM	SUPERVISOR	THS Pin <sup>(1)</sup>
M48Z512A	5V 4Mb LPSRAM	M40Z300	V <sub>SS</sub>
M48Z512AY	5V 4Mb LPSRAM	M40Z300	V <sub>OUT</sub>
M48Z512AV	3V 4Mb LPSRAM	M40Z300W	V <sub>SS</sub>

Note: 1. Connection of Threshold Select Pin (Pin 13) of SUPERVISOR (M40Z300/300W).

**MAXIMUM RATING**

Stressing the device above the rating listed in the “Absolute Maximum Ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is

not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

**Table 3. Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit	
T <sub>A</sub>	Ambient Operating Temperature	0 to 70	°C	
T <sub>STG</sub>	Storage Temperature (V <sub>CC</sub> Off, Oscillator Off)	−40 to 85	°C	
T <sub>BIAS</sub>	Temperature Under Bias	−40 to 70	°C	
T <sub>SLD</sub> <sup>(1,2)</sup>	Lead Solder Temperature for 10 seconds	260	°C	
V <sub>IO</sub>	Input or Output Voltages	−0.3 to 7	V	
V <sub>CC</sub>	Supply Voltage	M48Z512A/512AY	−0.3 to 7.0	V
		M48Z512AV	−0.3 to 4.6	V
I <sub>O</sub>	Output Current	20	mA	
P <sub>D</sub>	Power Dissipation	1	W	

- Note: 1. For DIP package: Soldering temperature not to exceed 260°C for 10 seconds (total thermal budget not to exceed 150°C for longer than 30 seconds).  
 2. For SO package: Reflow at peak temperature of 215°C to 225°C for < 60 seconds (total thermal budget not to exceed 180°C for between 90 to 120 seconds).

**CAUTION:** Negative undershoots below −0.3V are not allowed on any pin while in the Battery Back-up mode.  
**CAUTION:** Do NOT wave solder SOIC to avoid damaging SNAPHAT sockets.

## DC AND AC PARAMETERS

This section summarizes the operating and measurement conditions, as well as the DC and AC characteristics of the device. The parameters in the following DC and AC Characteristic tables are derived from tests performed under the Measure-

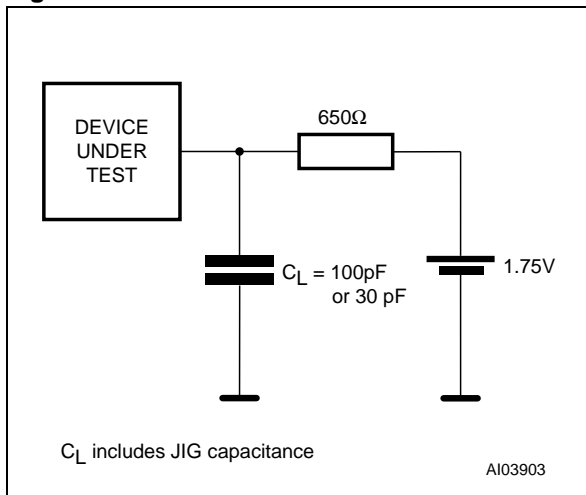
ment Conditions listed in the relevant tables. Designers should check that the operating conditions in their projects match the measurement conditions when using the quoted parameters.

**Table 4. Operating and AC Measurement Conditions**

Parameter	M48Z512A/512AY	M48Z512AV	Unit
Supply Voltage ( $V_{CC}$ )	4.75 to 5.5V or 4.5 to 5.5	3.0 to 3.6	V
Ambient Operating Temperature ( $T_A$ )	0 to 70	0 to 70	°C
Load Capacitance ( $C_L$ )	100	50	pF
Input Rise and Fall Times	$\leq 5$	$\leq 5$	ns
Input Pulse Voltages	0 to 3	0 to 3	V
Input and Output Timing Ref. Voltages	1.5	1.5	V

Note: Output Hi-Z is defined as the point where data is no longer driven.

**Figure 6. AC Measurement Load Circuit**



Note: Excluding open drain output pins; 50pF for M48Z512AV.

**Table 5. Capacitance**

Symbol	Parameter <sup>(1,2)</sup>	Min	Max	Unit
$C_{IN}$	Input Capacitance		10	pF
$C_{IO}^{(3)}$	Input / Output Capacitance		10	pF

Note: 1. Effective capacitance measured with power supply at 5V (M48Z512AY) or 3.3V (M48Z512AV); sampled only, not 100% tested.  
 2. Outputs deselected.  
 3. At 25°C.

**Table 6. DC Characteristics**

Sym	Parameter	Test Condition <sup>(1)</sup>	M48Z512A/Y		M48Z512AV		Unit
			-70		-85		
			Min	Max	Min	Max	
$I_{LI}^{(2)}$	Input Leakage Current	$0V \leq V_{IN} \leq V_{CC}$		$\pm 1$		$\pm 1$	$\mu A$
$I_{LO}^{(2)}$	Output Leakage Current	$0V \leq V_{OUT} \leq V_{CC}$		$\pm 1$		$\pm 1$	$\mu A$
$I_{CC}$	Supply Current	$\bar{E} = V_{IL}$ Outputs open		115		50	mA
$I_{CC1}$	Supply Current (Standby) TTL	$\bar{E} = V_{IH}$		10		4	mA
$I_{CC2}$	Supply Current (Standby) CMOS	$\bar{E} \geq V_{CC} - 0.2V$		5		3	mA
$V_{IL}$	Input Low Voltage		-0.3	0.8	-0.3	0.6	V
$V_{IH}$	Input High Voltage		2.2	$V_{CC} + 0.3$	2.2	$V_{CC} + 0.3$	V
$V_{OL}$	Output Low Voltage	$I_{OL} = 2.1mA$		0.4		0.4	V
$V_{OH}$	Output High Voltage	$I_{OH} = -1mA$	2.4		2.2		V

Note: 1. Valid for Ambient Operating Temperature:  $T_A = 0$  to  $70^\circ C$ ;  $V_{CC} = 4.75$  to  $5.5V$ ,  $4.5$  to  $5.5V$ , or  $3.0$  to  $3.6V$  (except where noted).  
 2. Outputs deselected.

## OPERATING MODES

The M48Z512A/Y/V also has its own Power-fail Detect circuit. The control circuitry constantly monitors the single  $V_{CC}$  supply for an out of tolerance condition. When  $V_{CC}$  is out of tolerance, the circuit write protects the SRAM, providing a high degree of data security in the midst of unpredictable system operation brought on by low  $V_{CC}$ . As  $V_{CC}$  falls below the switchover voltage ( $V_{SO}$ ), the control cir-

cuitry connects the battery which maintains data until valid power returns.

The ZEROPOWER<sup>®</sup> RAM replaces industry standard SRAMs. It provides the nonvolatility of PROMs without any requirement for special WRITE timing or limitations on the number of WRITES that can be performed.

**Table 7. Operating Modes**

Mode	$V_{CC}$	$\bar{E}$	$\bar{G}$	$\bar{W}$	DQ0-DQ7	Power
Deselect	4.75 to 5.5V or 4.5 to 5.5V or 3.0 to 3.6V	$V_{IH}$	X	X	High Z	Standby
WRITE		$V_{IL}$	X	$V_{IL}$	$D_{IN}$	Active
READ		$V_{IL}$	$V_{IL}$	$V_{IH}$	$D_{OUT}$	Active
READ		$V_{IL}$	$V_{IH}$	$V_{IH}$	High Z	Active
Deselect	$V_{SO}$ to $V_{PFD}$ (min) <sup>(1)</sup>	X	X	X	High Z	CMOS Standby
Deselect	$\leq V_{SO}^{(1)}$	X	X	X	High Z	Battery Back-up Mode

Note: X =  $V_{IH}$  or  $V_{IL}$ ;  $V_{SO}$  = Battery Back-up Switchover Voltage.

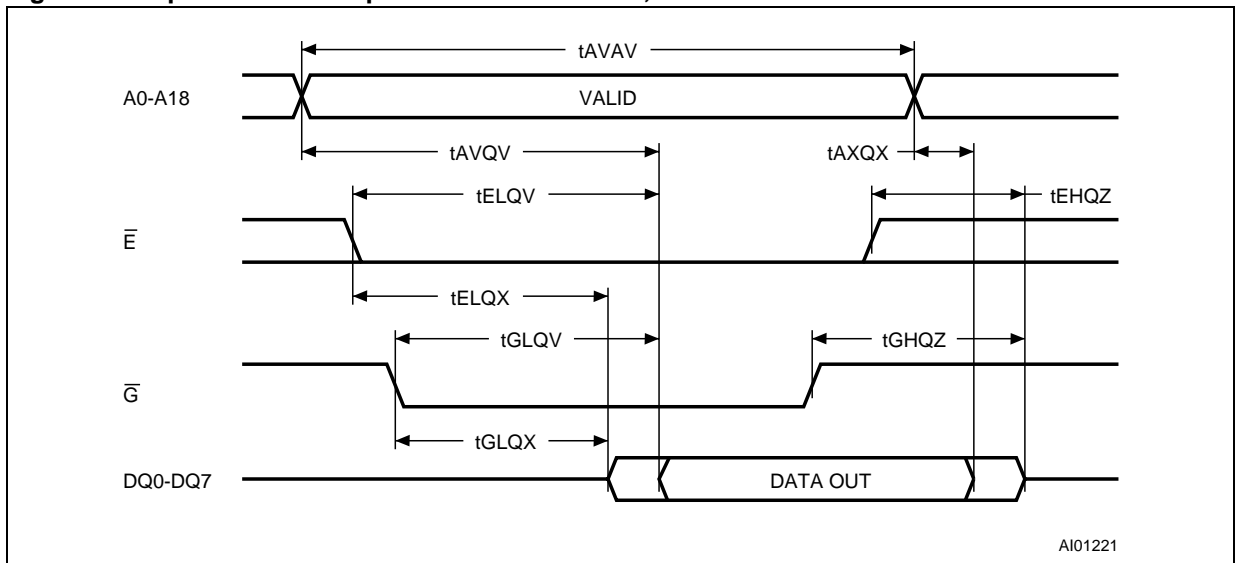
1. See Table 11, page 14 for details.

## READ Mode

The M48Z512A/Y/V is in the READ Mode whenever  $\bar{W}$  (WRITE Enable) is high and  $\bar{E}$  (Chip Enable) is low. The device architecture allows ripple-through access of data from eight of 4,194,304 locations in the static storage array. Thus, the unique address specified by the 19 Address Inputs defines which one of the 524,288 bytes of data is to be accessed. Valid data will be available at the Data I/O pins within Address Access time ( $t_{AVQV}$ ) after the last address input signal is stable, providing that the  $\bar{E}$  (Chip Enable) and  $\bar{G}$  (Output Enable) access times are also satisfied. If the  $\bar{E}$  and

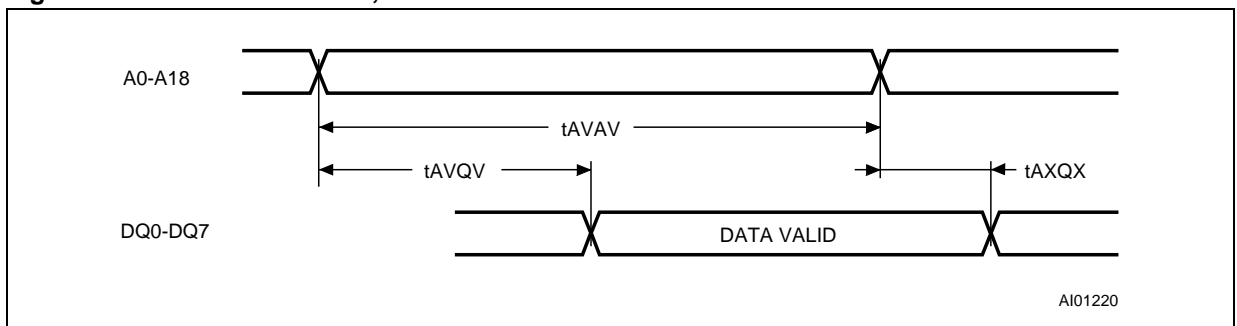
$\bar{G}$  access times are not met, valid data will be available after the later of Chip Enable Access time ( $t_{ELQV}$ ) or Output Enable Access Time ( $t_{GLQV}$ ). The state of the eight three-state Data I/O signals is controlled by  $\bar{E}$  and  $\bar{G}$ . If the outputs are activated before  $t_{AVQV}$ , the data lines will be driven to an indeterminate state until  $t_{AVQV}$ . If the Address Inputs are changed while  $\bar{E}$  and  $\bar{G}$  remain low, output data will remain valid for Output Data Hold time ( $t_{AXQX}$ ) but will go indeterminate until the next Address Access.

**Figure 7. Chip Enable or Output Enable Controlled, READ Mode AC Waveforms**



Note: WRITE Enable ( $\bar{W}$ ) = High.

**Figure 8. Address Controlled, READ Mode AC Waveforms**



Note: Chip Enable ( $\bar{E}$ ) and Output Enable ( $\bar{G}$ ) = Low, WRITE Enable ( $\bar{W}$ ) = High.

Table 8. READ Mode AC Characteristics

Symbol	Parameter <sup>(1)</sup>	M48Z512A/Y		M48Z512A/Y/V		Unit
		-70		-85		
		Min	Max	Min	Max	
t <sub>AVAV</sub>	READ Cycle Time	70		85		ns
t <sub>AVQV</sub>	Address Valid to Output Valid		70		85	ns
t <sub>ELQV</sub>	Chip Enable Low to Output Valid		70		85	ns
t <sub>GLQV</sub>	Output Enable Low to Output Valid		35		45	ns
t <sub>ELQX</sub> <sup>(2)</sup>	Chip Enable Low to Output Transition	5		5		ns
t <sub>GLQX</sub> <sup>(2)</sup>	Output Enable Low to Output Transition	5		5		ns
t <sub>EHQZ</sub> <sup>(2)</sup>	Chip Enable High to Output Hi-Z		30		35	ns
t <sub>GHQZ</sub> <sup>(2)</sup>	Output Enable High to Output Hi-Z		20		25	ns
t <sub>AXQX</sub>	Address Transition to Output Transition	5		5		ns

Note: 1. Valid for Ambient Operating Temperature: T<sub>A</sub> = 0 to 70°C; V<sub>CC</sub> = 4.75 to 5.5V, 4.5 to 5.5V, or 3.0 to 3.6V (except where noted).

2. C<sub>L</sub> = 5pF.

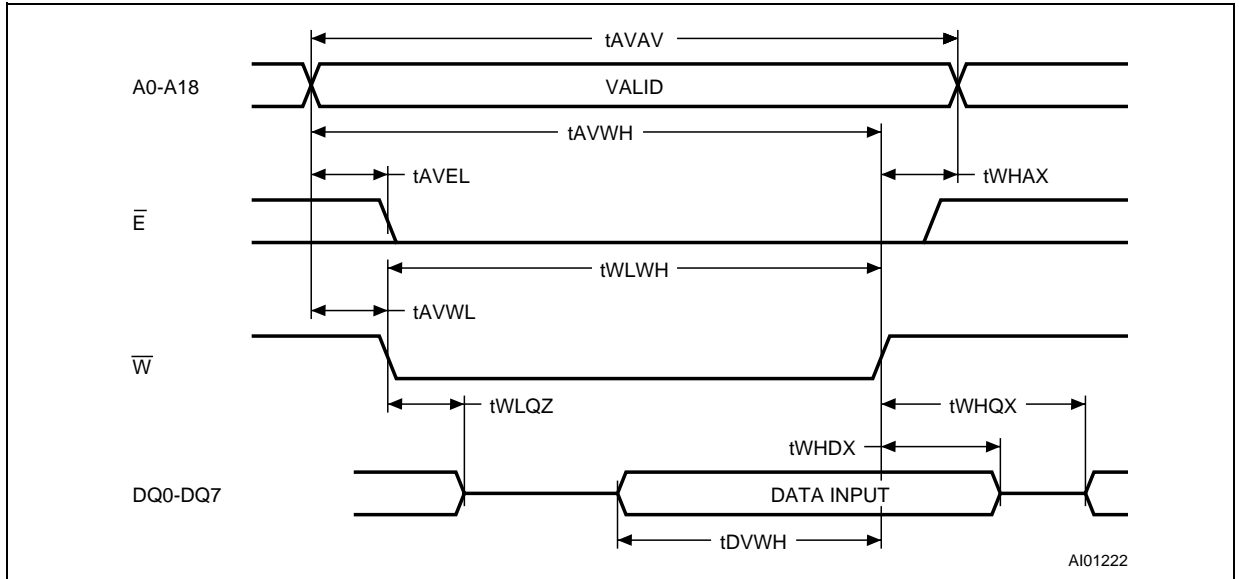
**WRITE Mode**

The M48Z512A/Y/V is in the WRITE Mode whenever  $\overline{W}$  and  $\overline{E}$  are active. The start of a WRITE is referenced from the latter occurring falling edge of  $\overline{W}$  or  $\overline{E}$ . A WRITE is terminated by the earlier rising edge of  $\overline{W}$  or  $\overline{E}$ .

The addresses must be held valid throughout the cycle.  $\overline{E}$  or  $\overline{W}$  must return high for a minimum of  $t_{E-HAX}$  from  $\overline{E}$  or  $t_{W-HAX}$  from  $\overline{W}$  prior to the initiation

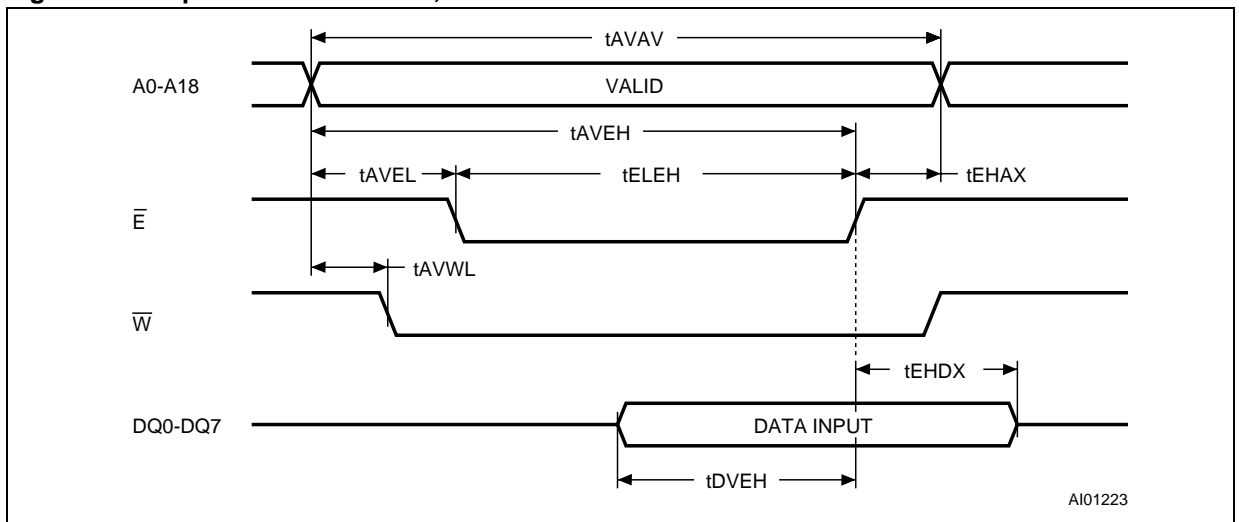
of another READ or WRITE cycle. Data-in must be valid  $t_{DVEH}$  or  $t_{DVWH}$  prior to the end of WRITE and remain valid for  $t_{EHDx}$  or  $t_{WHDx}$  afterward.  $\overline{G}$  should be kept high during WRITE cycles to avoid bus contention; although, if the output bus has been activated by a low on  $\overline{E}$  and  $\overline{G}$ , a low on  $\overline{W}$  will disable the outputs  $t_{WLQZ}$  after  $\overline{W}$  falls.

**Figure 9. WRITE Enable Controlled, WRITE AC Waveforms**



Note: Output Enable ( $\overline{G}$ ) = High.

**Figure 10. Chip Enable Controlled, WRITE AC Waveforms**



Note: Output Enable ( $\overline{G}$ ) = High.

**Table 9. WRITE Mode AC Characteristics**

Symbol	Parameter <sup>(1)</sup>	M48Z512A/Y		M48Z512A/Y/V		Unit
		-70		-85		
		Min	Max	Min	Max	
t <sub>AVAV</sub>	WRITE Cycle Time	70		85		ns
t <sub>AVWL</sub>	Address Valid to WRITE Enable Low	0		0		ns
t <sub>AVEL</sub>	Address Valid to Chip Enable Low	0		0		ns
t <sub>WLWH</sub>	WRITE Enable Pulse Width	55		65		ns
t <sub>ELEH</sub>	Chip Enable Low to Chip Enable High	55		75		ns
t <sub>WHAX</sub>	WRITE Enable High to Address Transition	5		5		ns
t <sub>EHAX</sub>	Chip Enable High to Address Transition	15		15		ns
t <sub>DVWH</sub>	Input Valid to WRITE Enable High	30		35		ns
t <sub>DVEH</sub>	Input Valid to Chip Enable High	30		35		ns
t <sub>WHDX</sub>	WRITE Enable High to Input Transition	0		0		ns
t <sub>EHDx</sub>	Chip Enable High to Input Transition	10		10		ns
t <sub>WLQZ</sub> <sup>(2,3)</sup>	WRITE Enable Low to Output Hi-Z		25		30	ns
t <sub>AVWH</sub>	Address Valid to WRITE Enable High	65		75		ns
t <sub>AVEH</sub>	Address Valid to Chip Enable High	65		75		ns
t <sub>WHQX</sub> <sup>(2,3)</sup>	WRITE Enable High to Output Transition	5		5		ns

Note: 1. Valid for Ambient Operating Temperature: T<sub>A</sub> = 0 to 70°C; V<sub>CC</sub> = 4.75 to 5.5V, 4.5 to 5.5V or 3.0 to 3.6V (except where noted).  
 2. C<sub>L</sub> = 5pF.  
 3. If  $\bar{E}$  goes low simultaneously with  $\bar{W}$  going low, the outputs remain in the high impedance state.

**Data Retention Mode**

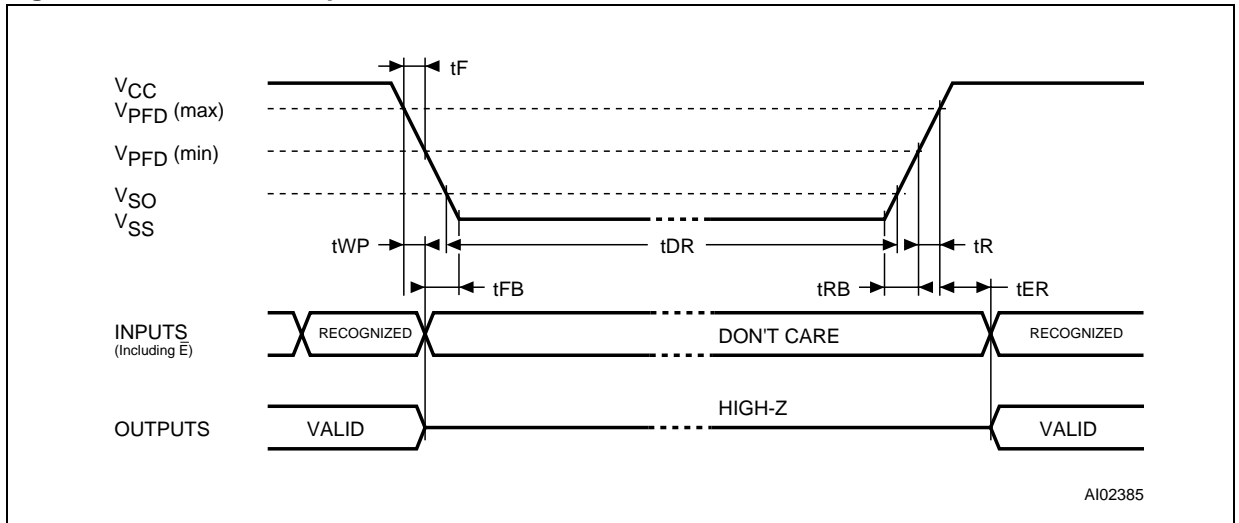
With valid  $V_{CC}$  applied, the M48Z512A/Y/V operates as a conventional BYTEWIDE™ static RAM. Should the supply voltage decay, the RAM will automatically power-fail deselect, write protecting itself  $t_{WP}$  after  $V_{CC}$  falls below  $V_{PFD}$ . All outputs become high impedance, and all inputs are treated as “don't care.”

If power fail detection occurs during a valid access, the memory cycle continues to completion. If the memory cycle fails to terminate within the time  $t_{WP}$ , write protection takes place. When  $V_{CC}$  drops below  $V_{SO}$ , the control circuit switches power to the internal energy source which preserves data.

The internal coin cell will maintain data in the M48Z512A/Y/V after the initial application of  $V_{CC}$  for an accumulated period of at least 10 years when  $V_{CC}$  is less than  $V_{SO}$ . As system power returns and  $V_{CC}$  rises above  $V_{SO}$ , the battery is disconnected, and the power supply is switched to external  $V_{CC}$ . Write protection continues for  $t_{ER}$  after  $V_{CC}$  reaches  $V_{PFD}$  to allow for processor stabilization. After  $t_{ER}$ , normal RAM operation can resume.

For more information on Battery Storage Life refer to the Application Note AN1012.

**Figure 11. Power Down/Up Mode AC Waveforms**



**Table 10. Power Down/Up AC Characteristics**

Symbol	Parameter <sup>(1)</sup>	Min	Max	Unit
$t_F^{(2)}$	$V_{PFD}(\text{max})$ to $V_{PFD}(\text{min})$ $V_{CC}$ Fall Time	300		$\mu\text{s}$
$t_{FB}^{(3)}$	$V_{PFD}(\text{min})$ to $V_{SS}$ $V_{CC}$ Fall Time	M48Z512A/Y	10	$\mu\text{s}$
		M48Z512AV	150	
$t_R$	$V_{PFD}(\text{min})$ to $V_{PFD}(\text{max})$ $V_{CC}$ Rise Time	10		$\mu\text{s}$
$t_{RB}$	$V_{SS}$ to $V_{PFD}(\text{min})$ $V_{CC}$ Rise Time	1		$\mu\text{s}$
$t_{WPT}$	Write Protect Time	M48Z512A/Y	40	150
		M48Z512AV	40	250
$t_{ER}$	$\bar{E}$ Recovery Time	40	120	ms

Note: 1. Valid for Ambient Operating Temperature:  $T_A = 0$  to  $70^\circ\text{C}$ ;  $V_{CC} = 4.75$  to  $5.5\text{V}$ ,  $4.5$  to  $5.5\text{V}$ , or  $3.0$  to  $3.6\text{V}$  (except where noted).  
 2.  $V_{PFD}(\text{max})$  to  $V_{PFD}(\text{min})$  fall time of less than  $t_F$  may result in deselection/write protection not occurring until  $200\mu\text{s}$  after  $V_{CC}$  passes  $V_{PFD}(\text{min})$ .  
 3.  $V_{PFD}(\text{min})$  to  $V_{SS}$  fall time of less than  $t_{FB}$  may cause corruption of RAM data.

**Table 11. Power Down/Up Trip Points DC Characteristics**

Symbol	Parameter <sup>(1,2)</sup>	Min	Typ	Max	Unit	
V <sub>PFDD</sub>	Power-fail Deselect Voltage	M48Z512A	4.5	4.6	4.75	V
		M48Z512AY	4.2	4.3	4.5	V
		M48Z512AV	2.8	2.9	3.0	V
V <sub>SO</sub>	Battery Back-up Switchover Voltage	M48Z512A/Y		3.0		V
		M48Z512AV		2.5		V
t <sub>DR</sub> <sup>(3)</sup>	Expected Data Retention Time	10			YEARS	

Note: 1. All voltages referenced to V<sub>SS</sub>.

2. Valid for Ambient Operating Temperature: T<sub>A</sub> = 0 to 70°C; V<sub>CC</sub> = 4.75 to 5.5V, 4.5 to 5.5V, or 3.0 to 3.6V (except where noted).

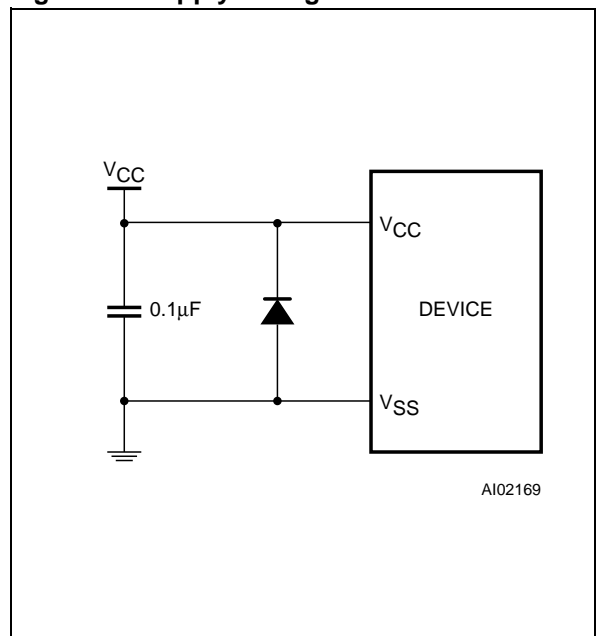
3. At 25°C; V<sub>CC</sub> = 0V.

### V<sub>CC</sub> Noise And Negative Going Transients

I<sub>CC</sub> transients, including those produced by output switching, can produce voltage fluctuations, resulting in spikes on the V<sub>CC</sub> bus. These transients can be reduced if capacitors are used to store energy which stabilizes the V<sub>CC</sub> bus. The energy stored in the bypass capacitors will be released as low going spikes are generated or energy will be absorbed when overshoots occur. A ceramic bypass capacitor value of 0.1µF (see Figure 12) is recommended in order to provide the needed filtering.

In addition to transients that are caused by normal SRAM operation, power cycling can generate negative voltage spikes on V<sub>CC</sub> that drive it to values below V<sub>SS</sub> by as much as one volt. These negative spikes can cause data corruption in the SRAM while in battery backup mode. To protect from these voltage spikes, ST recommends connecting a schottky diode from V<sub>CC</sub> to V<sub>SS</sub> (cathode connected to V<sub>CC</sub>, anode to V<sub>SS</sub>). (Schottky diode 1N5817 is recommended for through hole and MBRS120T3 is recommended for surface-mount).

**Figure 12. Supply Voltage Protection**



## PART NUMBERING

Table 12. Ordering Information Scheme

Example:	M48Z	512AY	-70	PM	1
<b>Device Type</b>					
M48Z					
<b>Supply Voltage and Write Protect Voltage</b>					
512A = $V_{CC} = 4.75$ to $5.5V$ ; $V_{PFD} = 4.5$ to $4.75V$					
512AY = $V_{CC} = 4.5$ to $5.5V$ ; $V_{PFD} = 4.2$ to $4.5V$					
512AV <sup>(1)</sup> = $V_{CC} = 3.0$ to $3.6V$ ; $V_{PFD} = 2.8$ to $3.0V$					
<b>Speed</b>					
-70 = 70ns (for M48Z512A/Y)					
-85 = 85ns (for M48Z512A/Y/V)					
<b>Package<sup>(2)</sup></b>					
PM = PMDIP32					
<b>Temperature Range</b>					
1 = 0 to 70°C					
9 = Extended Temperature <sup>(3)</sup>					

Note: 1. Contact Local Sales Office

2. The SOIC package (SOH28) requires the battery package (SNAPHAT<sup>®</sup>) which is ordered separately under the part number "M4Zxx-BR00SH" in plastic tube or "M4Zxx-BR00SHTR" in Tape & Reel form.

3. Contact Sales Offices for availability of Extended Temperature.

**Caution:** Do not place the SNAPHAT battery package "M4Zxx-BR00SH" in conductive foam as it will drain the lithium button-cell battery.

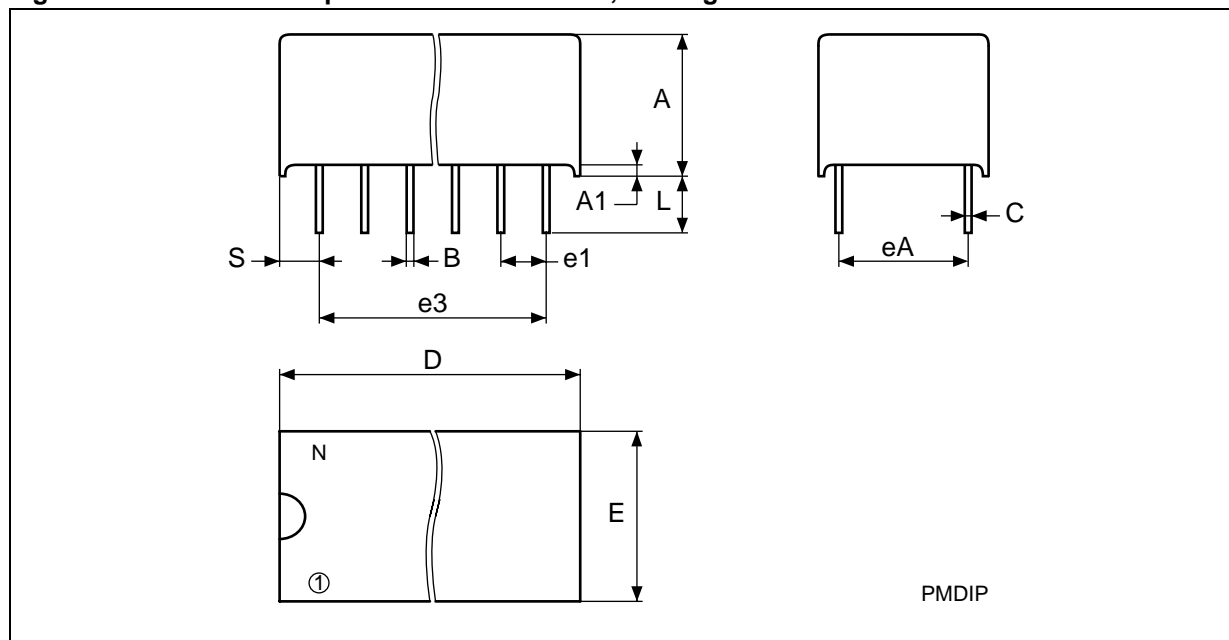
For a list of available options (e.g., Speed, Package) or for further information on any aspect of this device, please contact the ST Sales Office nearest to you.

Table 13. SNAPHAT Battery Table

Part Number	Description	Package
M4Z28-BR00SH	Lithium Battery (48mAh) SNAPHAT	SH
M4Z32-BR00SH	Lithium Battery (120mAh) SNAPHAT	SH

PACKAGE MECHANICAL INFORMATION

Figure 13. PMDIP32 – 32-pin Plastic DIP Module, Package Outline

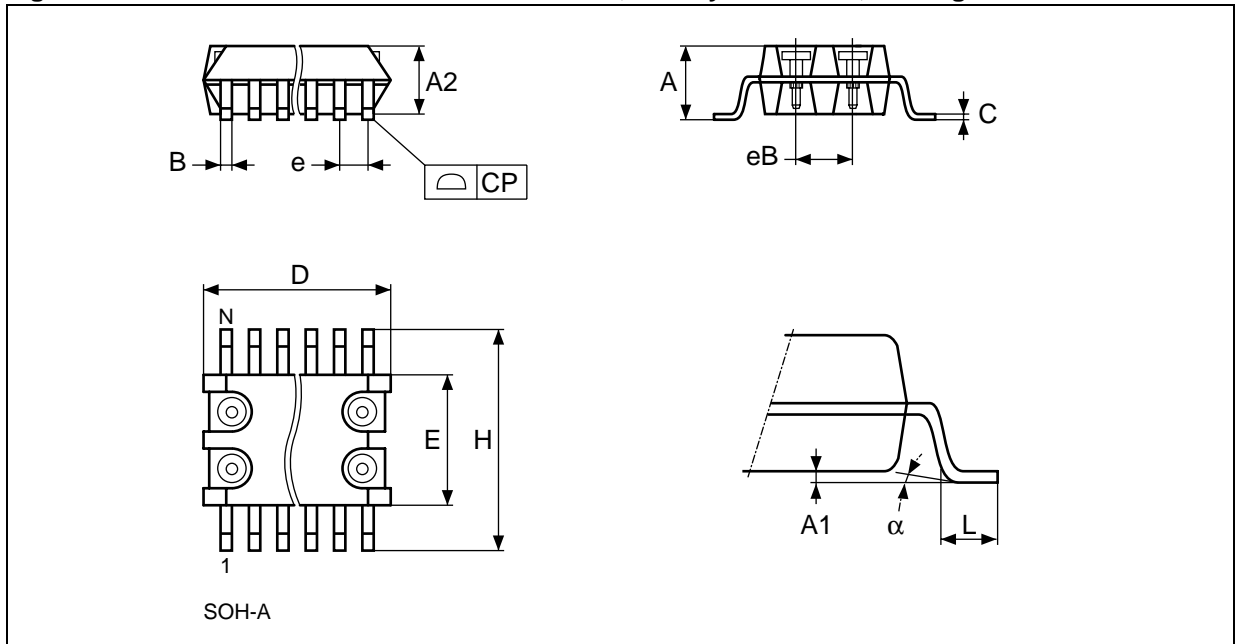


Note: Drawing is not to scale.

Table 14. PMDIP32 – 32-pin Plastic DIP Module, Package Mechanical Data

Symb	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A		9.27	9.52		0.365	0.375
A1		0.38	–		0.015	–
B		0.43	0.59		0.017	0.023
C		0.20	0.33		0.008	0.013
D		42.42	43.18		1.670	1.700
E		18.03	18.80		0.710	0.740
e1		2.29	2.79		0.090	0.110
e3		34.29	41.91		1.350	1.650
eA		14.99	16.00		0.590	0.630
L		3.05	3.81		0.120	0.150
S		1.91	2.79		0.075	0.110
N		32			32	

Figure 14. SOH28 – 28-lead Plastic Small Outline, battery SNAPHAT, Package Outline

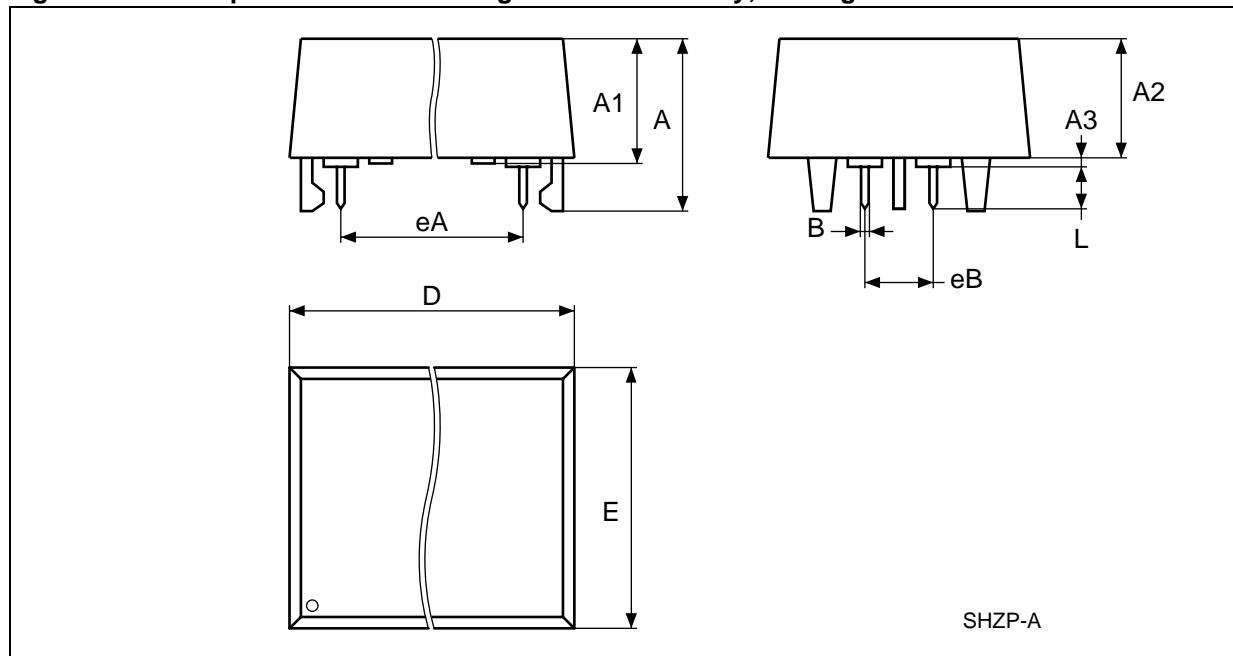


Note: Drawing is not to scale.

Table 15. SOH28 – 28-lead Plastic Small Outline, battery SNAPHAT, Package Mechanical Data

Symbol	mm			inch		
	Typ	Min	Max	Typ	Min	Max
A			3.05			0.120
A1		0.05	0.36		0.002	0.014
A2		2.34	2.69		0.092	0.106
B		0.36	0.51		0.014	0.020
C		0.15	0.32		0.006	0.012
D		17.71	18.49		0.697	0.728
E		8.23	8.89		0.324	0.350
e	1.27	–	–	0.050	–	–
eB		3.20	3.61		0.126	0.142
H		11.51	12.70		0.453	0.500
L		0.41	1.27		0.016	0.050
$\alpha$		0°	8°		0°	8°
N		28			28	
CP			0.10			0.004

Figure 15. SH – 4-pin SNAPHAT Housing for 48mAh Battery, Package Outline

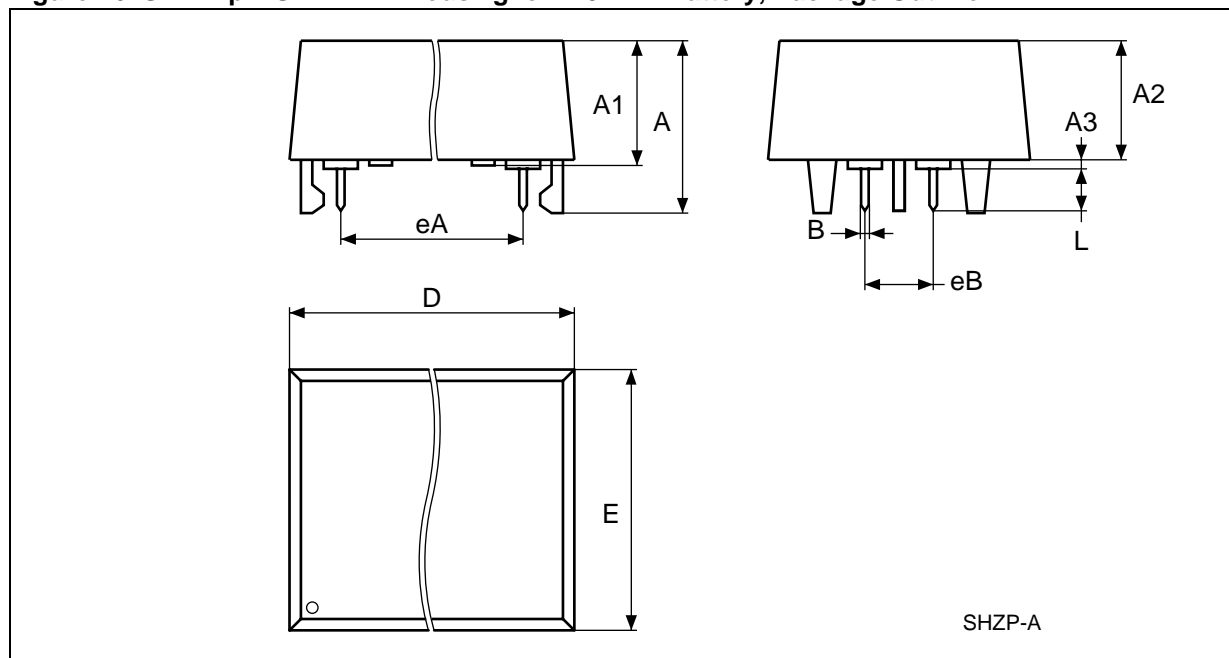


Note: Drawing is not to scale.

Table 16. SH – 4-pin SNAPHAT Housing for 48mAh Battery, Package Mechanical Data

Symb	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A			9.78			0.385
A1		6.73	7.24		0.265	0.285
A2		6.48	6.99		0.255	0.275
A3			0.38			0.015
B		0.46	0.56		0.018	0.022
D		21.21	21.84		0.835	0.860
E		14.22	14.99		0.560	0.590
eA		15.55	15.95		0.612	0.628
eB		3.20	3.61		0.126	0.142
L		2.03	2.29		0.080	0.090

Figure 16. SH – 4-pin SNAPHAT Housing for 120mAh Battery, Package Outline



Note: Drawing is not to scale.

Table 17. SH - 4-pin SNAPHAT Housing for 120mAh Battery, Package Mechanical Data

Symb	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A			10.54			0.415
A1		8.00	8.51		0.315	0.335
A2		7.24	8.00		0.285	0.315
A3			0.38			0.015
B		0.46	0.56		0.018	0.022
D		21.21	21.84		0.835	0.860
E		17.27	18.03		0.680	0.710
eA		15.55	15.95		0.612	0.628
eB		3.20	3.61		0.126	0.142
L		2.03	2.29		0.080	0.090

**REVISION HISTORY****Table 18. Revision History**

<b>Date</b>	<b>Rev. #</b>	<b>Revision Details</b>
March 2000	1.0	First Issue
19-Jul-00	1.1	M48Z12AV added
15-Jan-01	1.2	Changed LPSRAM device (Table 2)
19-Dec-01	2.0	Reformatted; added temperature information (Table 5, 6, 8, 9, 10, 11); remove chipset option from Ordering Information (Table 12); remove reference to "clock"
08-Feb-02	2.1	Remove 85ns speed grade (Table 6, 8, and 9)
29-May-02	2.2	Modify reflow time and temperature footnotes (Table 3)
18-Nov-02	2.3	Modified SMT text (Figure 2, 5; Table 2)
17-Sep-03	2.4	Remove references to M68xxx (obsolete) part (Figure 5; Table 2); update disclaimer

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